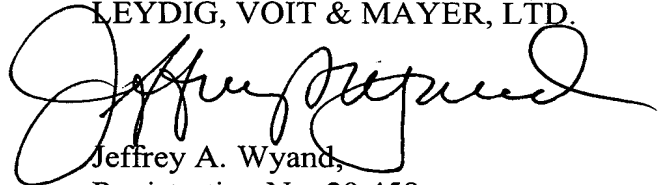


REMARKS

The foregoing amendments are made to correct minor translational errors and to meet United States requirements as to form. No new matter is added.

Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

AOYAGI et al.

Application No. Unassigned

Art Unit: Unassigned

Filed: November 14, 2001

Examiner: Unassigned

For: SEMICONDUCTOR
LASER DEVICE

**AMENDMENTS TO SPECIFICATION, CLAIMS, AND
ABSTRACT MADE VIA PRELIMINARY AMENDMENT**

Amendments to the paragraph beginning at page 1, line 5:

The present invention relates to a semiconductor laser device, and, more particularly, to a semiconductor laser device having a diffraction grating layer ~~of~~ with a phase shift structure used for optical communication.

Amendments to the paragraph beginning at page 1, line 14:

A distributed feedback semiconductor laser having a diffraction grating provided in the direction of an optical waveguide effects optical feedback corresponding to the period of the diffraction grating, thus enabling single-mode emission. ~~Then~~ Thus, the distributed feedback semiconductor laser has been developed ~~for~~ for optical communication.

Amendments to the paragraph beginning at page 1, line 20:

Japanese Patent Application Laid-Open No. Hei. 1-155677/1989 describes an invention pertaining to a distributed feedback (DFB) semiconductor laser. In relation to a related-art DFB semiconductor laser, the positional relationship between reflection surfaces provided at both ends of the laser in the direction of an optical waveguide and the phase of the diffraction grating affects an oscillation characteristic of having a single longitudinal mode. For this reason, a $\lambda/4$ phase-shifted structure has been employed, and both end surfaces of the laser are covered with a non-reflection coating, thereby minimizing the reflectance of the end faces. If the product of a coupling factor κ and a cavity length L , that is, κL , is not in the vicinity of a value of 1.25, an axial hole burning phenomenon arises, and, in turn, deteriorates a single longitudinal mode characteristic of the laser. In order to solve the problem, there is described a DFB semiconductor laser, in which the reflectance of optical power of one end surface is set to 30% and the reflectance of the other end is set to 5 to 15%, thereby achieving a κL value of $0.4 \leq \kappa L \leq 1.3$.

Amendments to the paragraph beginning at page 2, line 5:

The related-art DFB semiconductor laser induces an axial hole burning phenomenon when the product of a coupling factor κ and a cavity length L , that is, κL , is not in the vicinity of a value of 1.25, thus deteriorating a single longitudinal mode characteristic of the laser. A high-precision, non-reflection coating technique has been pursued, and there has been devised a window structure for embedding end-face sections of a waveguide for minimizing the reflectance of the end faces. In light of the above-described drawbacks, Japanese Patent Application Laid-Open No. Hei. 2-20087/1990 describes a DFB semiconductor laser which is comparatively easy to manufacture and is of has a structure capable of realizing a single longitudinal mode at high yield. The DFB semiconductor laser has one or more phase shift regions within 20% of the resonance length with reference to the center of the cavity. The reflectance of respective end faces is set to 5 to 15%, and the product κL is set to the range of $0.6 \leq \kappa L \leq 1.0$.

Amendments to the paragraph beginning at page 2, line 20:

In relation to the related-art DFB semiconductor laser, the diffraction grating is adjusted such that the product of a coupling factor κ and a cavity length $L_{\lambda/2}$ that is, κL , assumes a value of 1.2 to 1.3. However, such a semiconductor laser involves a high oscillation threshold current and it tends to saturate in optical output more than other DFB semiconductor lasers under high-temperature operation. To solve the problem, Japanese Patent Application Laid-Open No. Hei. 2-90688/1990 describes a $\lambda/4$ phase-shifted DFB semiconductor laser. In relation to the laser, an optical guide layer is provided between an active layer and a cladding layer, wherein the thickness of the optical guide layer changes at a period which is an ~~integral~~ integer multiple of half the wavelength of traveling light. Further, the energy gap of the optical guide layer is greater than that of the active layer and smaller than that of the cladding layer. The product of a coupling factor κ and a cavity length $L_{\lambda/2}$ that is, κL , is set to a value of 1.5 to 2.5.

Amendments to the paragraph beginning at page 3, line 3:

In relation to the related-art DFB semiconductor laser, a multilayer dielectric film is formed on an output end face of the laser, thereby reducing optically-induced return noise. This also drastically reduces optical output from the output end face. In order to reduce the optically-induced return noise and to ensure sufficient optical output, Japanese Patent Application Laid-Open No. Hei. 5-48197/1993 describes a $\lambda/4$ phase-shifted DFB semiconductor laser which is constructed as follows. Namely, the output end face of the laser is covered with a non-reflective coating. Provided that a length from a rear end face to a $\lambda/4$ phase shift point is taken as L_s and the length of a laser cavity is taken as L , $\lambda/4$ phase shift is located in a position where $0.2 \leq L_s/L \leq 0.4$ is obtained. Further, the product of a coupling factor κ and a cavity length $L_{\lambda/2}$ that is, κL , is set to the range of $2 \leq \kappa L \leq 4$. The laid-open patent publication states that, when measurement was effected through use of an element having a cavity length of 300 μm , superior single-mode oscillation was ascertained to arise even at a κL value of about 3, and good current-light output was

obtained.

Amendments to the paragraph beginning at page 3, line 21:

Japanese Patent Application Laid-Open No. Hei. 6-204607/1994 describes an improvement in the yield and efficiency of a DFB semiconductor laser, including an analog modulation distortion characteristic and a single-mode characteristic. In order to obtain a low-cost, low-distortion analog modulation DFB semiconductor laser, there is employed a structure wherein the reflectance of the front end face of the cavity is less than 5% and wherein the product of a coupling factor κ and a cavity length L , that is, κL , is set to the range of $0.4 \leq \kappa L \leq 1.0$.

Amendments to the paragraph beginning at page 3, line 30:

Further, the related-art $\lambda/4$ phase-shifted DFB semiconductor laser element has encountered difficulty in achieving compatibility-~~among~~ of high stability of single mode, a high-yield characteristic, and a high efficiency-and-output characteristic. For this reason, Japanese Patent Application Laid-Open No. Hei. 11-68220/1999 describes a DFB semiconductor laser, wherein a low-reflection film is formed on an optical output end face and wherein a high-reflection film is formed on the other end face. Further, a diffraction grating is formed in a part of the element in the direction toward the cavity. The length of an area where the diffraction grating is to be fabricated is set to 52% to 64% the element length. The product of a coupling factor of the diffraction grating and the length of the diffraction grating fabrication area is set to the range of 0.8 to 2.

Amendments to the paragraph beginning at page 5, line 9:

On pp. 89 to 90, 2000 IEEE 17TH International Semiconductor Laser Conference 25 to 28 September 2000 Hyatt Monterey, Monterey Ca, CONFERENCE DIGEST P13, G. Sakaino *et al.* reported a phase-shifted DFB semiconductor laser. The laser has an active layer made of ~~InGaAsP~~ InGaAsP-based material, a cavity length as short as 200

μm , and a diffraction grating ~~of having~~ a high κL value. An active layer of the laser does not have any function of a diffraction grating. In relation to the laser, the relaxation oscillation frequency remains at a value of 12.0 GHz or thereabouts.

Amendments to the paragraph beginning at page 5, line 22:

In order to achieve a transmission rate of 10 Gb/s, ~~acquisition of a~~ relaxation oscillation frequency of 30 GHz or more is desired. However, it is empirically seen that, if a relaxation oscillation frequency of 15 GHz or more is not obtained, a sufficient eye-pattern opening will not be obtained, thus inducing non-negligible deterioration in receiving sensitivity.

Amendments to the paragraph beginning at page 5, line 28:

Moreover, IEEE PHOTONICS TECHNOLOGY LETTERS, VOL. 7, NO. 10, OCTOBER 1995, PP. 1119 to 1121 ~~states~~ reports a multiple reflection short-length cavity of active layer isolation type having a $\lambda/4$ phase-shifted structure.

Amendments to the paragraph beginning at page 7, line 24:

Fig. 5 is a graph showing the dependence, γ , on the length L of the diffraction grating region, γ , of the relaxation oscillation frequency f_r using as a parameter the coupling coefficient κ of the semiconductor laser according to an embodiment of the present invention.

Amendments to the existing claims:

1. (Amended) A semiconductor laser device comprising:
a semiconductor substrate of a first conductivity type;
a first cladding layer of the first conductivity type ~~provided~~ disposed on the semiconductor substrate;

an active layer ~~provided~~ disposed on the first cladding layer and having uniformly flat upper and lower boundary surfaces in ~~the direction of~~ an optical waveguide direction;

a second cladding layer of a second conductivity type ~~provided~~ disposed on the active layer; and

a diffraction grating layer having a phase-shifted structure, ~~provided in the direction of the optical waveguide direction, between the first cladding layer and the active layer or between~~ and one of the first and second cladding layer and the active layer layers, wherein

~~the length L of the diffraction grating layer has a length in the direction of the optical waveguide is taken as~~ direction L $L \leq 260 \mu\text{m}$;

a mean coupling factor κ of a diffraction grating layer is ~~taken as~~ $\kappa \geq 150 \text{ cm}^{-1}$; and

~~a value κL , which is the product of the length L and the mean coupling factor κ , is taken as~~ satisfies $5.6 > \kappa L > 3.0$.

2. (Amended) The semiconductor laser device according to claim 1, wherein ~~the power threshold gain α_{th} per unit length in a principal axial mode is set to~~ satisfies $7 \text{ cm}^{-1} \leq \alpha_{th} \leq 51 \text{ cm}^{-1}$.

3. (Amended) The semiconductor laser device according to claim 1 ~~or 2~~, further comprising: a heavily-doped p-type region ~~doped with p-type impurities at~~ having a carrier concentration of 10^{18} cm^{-3} in at least a portion of a p-type layer ~~of p-conductivity type located proximate to an active layer or~~ at least a portion of the active layer.

4. (Amended) The semiconductor laser device according to claim 2, further comprising: a heavily-doped p-type region ~~doped with p-type impurities at~~ having a carrier concentration of 10^{18} cm^{-3} in at least a portion of a p-type layer ~~of p-conductivity type located proximate to an active layer or~~ at least a portion of the active layer.

5. (Amended) The semiconductor laser device according to ~~claims~~ claim 1,
wherein ~~there is further achieved~~

$$\lambda_p - 100 \leq \lambda_g \leq \lambda_p + 100,$$

~~provided that~~ where a composition wavelength of the diffraction grating layer is ~~taken as~~
 λ_g (nm) and an oscillation wavelength is ~~taken as~~ λ_p (nm).

6. (Amended) The semiconductor laser device according to ~~claims~~ claim 2,
wherein ~~there is further achieved~~

$$\lambda_p - 100 \leq \lambda_g \leq \lambda_p + 100,$$

~~provided that~~ where a composition wavelength of the diffraction grating layer is ~~taken as~~
 λ_g (nm) and an oscillation wavelength is ~~taken as~~ λ_p (nm).

7. (Amended) The semiconductor laser device according to ~~claims~~ claim 3,
wherein ~~there is further achieved~~

$$\lambda_p - 100 \leq \lambda_g \leq \lambda_p + 100,$$

~~provided that~~ where a composition wavelength of the diffraction grating layer is ~~taken as~~
 λ_g (nm) and an oscillation wavelength is ~~taken as~~ λ_p (nm).

8. (Amended) The semiconductor laser device according to ~~claims~~ claim 4,
wherein ~~there is further achieved~~

$$\lambda_p - 100 \leq \lambda_g \leq \lambda_p + 100,$$

~~provided that~~ where a composition wavelength of the diffraction grating layer is ~~taken as~~
 λ_g (nm) and an oscillation wavelength is ~~taken as~~ λ_p (nm).

9. (Amended) The semiconductor laser device according to ~~claims~~ claim 1,
wherein ~~the length of a highly-refractive portion constituting diffraction grating of the~~
~~diffraction grating layer is set so as to become~~ has a length longer than that of a low-
refractive portion of the diffraction grating layer in the ~~direction of the~~ optical waveguide
direction.

10. (Amended) The semiconductor laser device according to ~~claims~~ claim 2, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

11. (Amended) The semiconductor laser device according to ~~claims~~ claim 3, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

12. (Amended) The semiconductor laser device according to ~~claims~~ claim 4, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

13. (Amended) The semiconductor laser device according to ~~claims~~ claim 5, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

14. (Amended) The semiconductor laser device according to ~~claims~~ claim 6, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

15. (Amended) The semiconductor laser device according to ~~claims~~ claim 7, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

16. (Amended) The semiconductor laser device according to ~~claims~~ claim 8, wherein ~~the length of a highly-refractive portion constituting diffraction grating of the diffraction grating layer is set so as to become~~ has a length longer than that of a low-refractive portion of the diffraction grating layer in the ~~direction of the optical waveguide~~ direction.

Amendments to the abstract:

ABSTRACT OF THE DISCLOSURE

An n-InP second upper cladding layer ~~22~~ is laid on a p-InP lower cladding layer ~~14~~ while an active layer ~~16~~ whose having upper and lower boundary surfaces that are uniformly flat in ~~the direction of an~~ optical waveguide direction is interposed therebetween. A diffraction layer ~~20~~ having a phase-shifted structure ~~provided~~ in the ~~direction of~~ optical waveguide direction is interposed between the lower cladding layer ~~14~~ and the active layer ~~16~~, or between the second upper cladding layer ~~22~~ and the active layer ~~16~~. The length L of the diffraction grating layer ~~20~~ in the direction of ~~an~~ the optical waveguide is ~~taken as~~ $L \leq 260 \mu\text{m}$; a mean coupling factor κ of a diffraction grating layer is ~~taken as~~ $\kappa \geq 150 \text{ cm}^{-1}$; and ~~a value κL , which is the product of the length L and the mean coupling factor κ , is taken as~~ satisfies $5.6 > \kappa L > 3.0$.